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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, TSI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 9x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl15z64vfm4r

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: PKL15 and MKL15

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	 M = Fully qualified, general market flow P = Prequalification
KL##	Kinetis family	• KL15
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	 32 = 32 KB 64 = 64 KB 128 = 128 KB 256 = 256 KB

Table continues on the next page

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min. Max.		Unit
I _{WP}	Digital I/O weak pullup/ pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	_	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

- Operating ratings apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Тур.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μΑ

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

General

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	Low-voltage warning thresholds — low range					1
V _{LVW1L}	Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	 Level 3 falling (LVWV=10) 	1.94	2.00	2.06	V	
V _{LVW4L}	Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	_	±40		mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad				1
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -5 mA	V _{DD} – 0.5	_	V	
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OH}} = -1.5 \text{ mA}$	V _{DD} – 0.5	_	V	
V _{OH}	Output high voltage — High drive pad				1
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -18 mA	V _{DD} – 0.5	_	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OH} = -6 mA	V _{DD} – 0.5	_	V	
I _{OHT}	Output high current total for all ports	_	100	mA	
V _{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 5 mA	—	0.5	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 1.5 mA	—	0.5	V	
V _{OL}	Output low voltage — High drive pad				1
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 18 mA	—	0.5	V	
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OL}} = 6 \text{ mA}$	—	0.5	V	
I _{OLT}	Output low current total for all ports	_	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	_	1	μA	2
l _{IN}	Input leakage current (per pin) at 25 °C	_	0.025	μA	2
I _{IN}	Input leakage current (total all pins) for full temperature range	—	65	μA	2
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	

Table 3. Voltage and current operating behaviors

Table continues on the next page...

Table 5.	Power	consumpti	ion opera	iting beha	viors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V		300	745	μA	5, 4
I _{DD_VLPW}	Very low power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	_	135	496	μA	5
I _{DD_STOP}	Stop mode current at 3.0 V					
	at 25 °C	_	345	490		
	at 50 °C	_	357	827	μΑ	
	at 70 °C	_	392	869		
	at 85 °C	_	438	927		
	at 105 °C	_	551	1065		
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	at 25 °C	_	4.4	16		
	at 50 °C	_	10	35	μA	
	at 70 °C	_	20	50		
	at 85 °C	_	37	112		
	at 105 °C	_	81	201		
I _{DD_LLS}	Low leakage stop mode current at 3.0 V				_	
	at 25 °C	_	1.9	3.7	μΑ	
	at 50 °C	_	3.6	39		
	at 70 °C	_	6.5	43		
	at 85 °C	_	13	49		
	at 105 °C	_	30	69		
I _{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	at 25 °C	_	1.4	3.2	μΑ	
	at 50 °C	_	2.5	19		
	at 70 °C	—	5.1	21		
	at 85 °C	_	9.2	26		
	at 105 °C	_	21	38		
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0V					
	at 25°C	—	0.7	1.4		
	at 50°C	—	1.3	13	μΑ	
	at 70°C	_	2.3	14		
	at 85°C	—	5.1	17		
	at 105°C	—	13	25		

Table continues on the next page...

Symbol	Description	Temperature (°C)				Unit		
		-40	25	50	70	85	105	
IEREFSTEN32KHz	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN							
	entering all modes with the crystal	440	490	540	560	570	580	
	enabled.	440	490	540	560	570	580	
	VLLS1	490	490	540	560	570	680	nA
	VLLS3	510	560	560	560	610	680	
	LLS	510	560	560	560	610	680	
	VLPS							
	STOP							
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	22	22	22	22	22	22	μΑ
IRTC	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption. MCGIRCLK (4MHz internal reference clock)	66	66	66	66	66	66	μΑ
	OSCERCLK (4MHz external crystal)	214	237	246	254	260	268	
ITPM	I PM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.							μΑ
	MCGIRCLK (4MHz internal reference clock)	86	86	86	86	86	86	
	OSCERCLK (4MHz external crystal)	235	256	265	274	280	287	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA

Table 6. Low power mode peripheral adders — typical value (continued)

Table continues on the next page...



Symbol	Description		Temperature (°C)					Unit
		-40	25	50	70	85	105	
I _{ADC}	ADC peripheral adder combining the measured values at VDD and VDDA by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μA

 Table 6. Low power mode peripheral adders — typical value (continued)

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

General



Figure 3. VLPR mode current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 64-pin LQFP package

Symbol	Description	Frequency band (MHz)	Тур.	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	13	dBµV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	15	dBµV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	12	dBµV	
V _{RE4}	Radiated emissions voltage, band 4	500-1000	7	dBµV	
V _{RE_IEC}	IEC level	0.15–1000	М		2, 3

 Determined according to IEC Standard 61967-1, Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions and IEC Standard 61967-2, Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions – TEM Cell and Wideband TEM Cell Method. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

Peripheral operating requirements and behaviors

Symbol	Description		Min.	Тур.	Max.	Unit	Notes
f _{dco_t_DMX32}	DCO output	Low range (DRS = 00)	_	23.99	—	MHz	5, 6
	frequency	$732 \times f_{fll_ref}$					
		Mid range (DRS = 01)	_	47.97	—	MHz	
		$1464 \times f_{fll_ref}$					
J _{cyc_fll}	FLL period jitter		—	180	—	ps	7
	• f _{VCO} = 48 M	Hz					
t _{fll_acquire}	FLL target frequer	ncy acquisition time	—	—	1	ms	8
		PI	L				
f _{vco}	VCO operating fre	quency	48.0	—	100	MHz	
I _{pll}	PLL operating cur PLL at 96 M MHz, VDIV	rent Hz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = 2 multiplier = 48)	_	1060	_	μA	9
I _{pll}	PLL operating cur PLL at 48 M MHz, VDIV	rent Hz ($f_{osc_hi_1} = 8 \text{ MHz}, f_{pll_ref} = 2$ multiplier = 24)	_	600	_	μΑ	9
f _{pll_ref}	PLL reference free	quency range	2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (F	RMS)					10
	• f _{vco} = 48 MH	lz	—	120	-	ps	
	• f _{vco} = 100 M	Hz	—	50	_	ps	
J _{acc_pll}	PLL accumulated	jitter over 1µs (RMS)					10
	• f _{vco} = 48 MH	lz	—	1350	_	ps	
	• f _{vco} = 100 M	Hz	—	600	_	ps	
D _{lock}	Lock entry frequer	ncy tolerance	± 1.49	—	± 2.98	%	
D _{unl}	Lock exit frequence	y tolerance	± 4.47	—	± 5.97	%	
t _{pll_lock}	Lock detector dete	ection time			150 × 10 ⁻⁶ + 1075(1/ f _{pll_ref})	S	11

Table 12. MCG specifications (continued)

- 1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
- 2. The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, $f_{ints_{t}}$.
- 3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
- The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco t}) over voltage and temperature must be considered.
- 5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
- 6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 7. This specification is based on standard deviation (RMS) of period or frequency.
- 8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

9. Excludes any oscillator currents that are also consuming power while PLL is in operation.

- 10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
- 11. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

Peripheral operating requirements and behaviors

6.4.1.2 Flash timing specifications — commands Table 16. Flash command timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{rd1sec1k}	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t _{pgmchk}	Program Check execution time	—	—	45	μs	1
t _{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t _{pgm4}	Program Longword execution time	_	65	145	μs	
t _{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t _{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t _{rdonce}	Read Once execution time	_	_	25	μs	1
t _{pgmonce}	Program Once execution time	—	65	_	μs	
t _{ersall}	Erase All Blocks execution time	—	62	500	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	_	_	30	μs	1

1. Assumes 25MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors Table 17. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 18. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes	
Program Flash							
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years		
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	_	years		
n _{nvmcycp}	Cycling endurance	10 K	50 K	_	cycles	2	

 Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40°C \leq T_i \leq 125°C.

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
	ADC	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t _{ADACK} = 1/
	asynchronous	• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	f _{ADACK}
f _{ADACK}		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter	for sample t	imes			
TUE	Total unadjusted	12-bit modes		±4	±6.8	LSB ⁴	5
	error	 <12-bit modes 	_	±1.4	±2.1		
DNL	Differential non-	12-bit modes	_	±0.7	-1.1 to +1.9	LSB ⁴	5
	linearity				-0.3 to 0.5		
		 <12-bit modes 		±0.2			
INL	Integral non-	12-bit modes	—	±1.0	-2.7 to +1.9	LSB ⁴	5
	linearity				-0.7 to +0.5		
		 <12-bit modes 	—	±0.5			
E _{FS}	Full-scale error	12-bit modes	—	-4	-5.4	LSB ⁴	V _{ADIN} =
		 <12-bit modes 		-1.4	-1.8		V _{DDA}
Eq	Quantization	16-bit modes		-1 to 0	_	LSB ⁴	
	error	• ≤1312-bit modes	_	_	±0.5		
ENOB	Effective number	16-bit differential mode					6
	of bits	• Avg = 32	12.8	14.5	—	bits	
		• Avg = 4	11.9	13.8	—	bits	
		16-bit single-ended mode					
		• Avg = 32	12.2	13.0		bite	
		• Avg = 4	11 /	13.1		bite	
	Signal-to-noise	See ENOB	11.7	10.1		0113	
SINAD	plus distortion		6.02	2 × ENOB +	1.76	dB	
THD	Total harmonic	16-bit differential mode					7
	distortion	• Avg = 32	_	-94	—	dB	
		16-bit single-ended mode		05		10	
		• Avg = 32	_	-85	_	aв	
SFDR	Spurious free	16-bit differential mode					7
	dynamic range	• Avg = 32	82	95		dB	
		16-bit single-ended mode					
			78	90	-	dB	
		Avg = 32					

Table 20.	16-bit ADC characteristics ($V_{\text{REFH}} = V_{\text{DDA}}$	$V_{\text{REFL}} = V_{SSA}$	(continued)
			* REFL - * 33A/	

Table continues on the next page...



Typical ADC 16-bit Single-Ended ENOB vs ADC Clock 100Hz, 90% FS Sine Input

Figure 8. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.2 CMP and 6-bit DAC electrical specifications Table 21. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V _{DD}	Supply voltage	1.71	—	3.6	V
I _{DDHS}	Supply current, high-speed mode (EN = 1, PMODE = 1)	_	_	200	μA
I _{DDLS}	Supply current, low-speed mode (EN = 1, PMODE = 0)	_	—	20	μA
V _{AIN}	Analog input voltage	V _{SS}	—	V _{DD}	V
V _{AIO}	Analog input offset voltage	_	—	20	mV
V _H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	 CR0[HYSTCTR] = 01 	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	 CR0[HYSTCTR] = 11 	—	30	—	mV
V _{CMPOh}	Output high	V _{DD} – 0.5	—	_	V
V _{CMPOI}	Output low	_	—	0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns

Table continues on the next page ...

6.6.3.1 12-bit DAC operating requirements Table 22. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage	1.71	3.6	V	
V _{DACR}	Reference voltage	1.13	3.6	V	1
T _A	Temperature	Operating t range of t	emperature he device	°C	
CL	Output load capacitance	_	100	pF	2
١L	Output load current		1	mA	

1. The DAC reference can be selected to be V_{DDA} or the voltage output of the VREF module (VREF_OUT)

2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

6.6.3.2 12-bit DAC operating behaviors Table 23. 12-bit DAC operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA_DACL}	Supply current — low-power mode	_	_	250	μΑ	
I _{DDA_DACH} P	Supply current — high-speed mode	_	—	900	μΑ	
tDACLP	Full-scale settling time (0x080 to 0xF7F) — low-power mode		100	200	μs	1
t _{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	_	15	30	μs	1
t _{CCDACLP}	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	_	0.7	1	μs	1
V _{dacoutl}	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000		—	100	mV	
V _{dacouth}	DAC output voltage range high — high- speed mode, no load, DAC set to 0xFFF	V _{DACR} -100	—	V _{DACR}	mV	
INL	Integral non-linearity error — high speed mode	_	_	±8	LSB	2
DNL	Differential non-linearity error — V _{DACR} > 2 V	_	—	±1	LSB	3
DNL	Differential non-linearity error — V _{DACR} = VREF_OUT	_	—	±1	LSB	4
VOFFSET	Offset error	_	±0.4	±0.8	%FSR	5
E _G	Gain error	_	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \ge 2.4 V$	60	—	90	dB	
T _{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T _{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance load = $3 \text{ k}\Omega$	—	—	250	Ω	

Table continues on the next page ...

Peripheral operating requirements and behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
SR	Slew rate -80h→ F7Fh→ 80h				V/µs	
	 High power (SP_{HP}) 	1.2	1.7	_		
	Low power (SP _{LP})	0.05	0.12	_		
BW	3dB bandwidth				kHz	
	• High power (SP _{HP})	550	_	_		
	• Low power (SP _{LP})	40	_	_		

Table 23. 12-bit DAC operating behaviors (continued)

- 1. Settling within ±1 LSB
- 2. The INL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 3. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 4. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV with V_{DDA} > 2.4 V
- 5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} 100 mV 6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device





Peripheral operating requirements and behaviors



NOTE: Not defined!









6.8.2 I²C

See General switching specifications.

6.8.3 UART

See General switching specifications.

KL15 Sub-Family Data Sheet Data Sheet, Rev. 3, 9/19/2012.

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 28. TSI electrical specifications

Symbol	Description	Min.	Туре	Мах	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	μA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	μA
TSI_EN	Power consumption in enable mode		100		μA
TSI_DIS	Power consumption in disable mode		1.2	_	μA
TSI_TEN	TSI analog enable time		66		μs
TSI_CREF	TSI reference capacitor	_	1.0	_	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	0.19		1.03	V

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to www.freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ASA00473D
48-pin QFN	98ASA00466D
64-pin LQFP	98ASS23234W
80-pin LQFP	98ASS23174W

8 Pinout

8.1 KL15 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALTO	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	1	_	1	PTE0	DISABLED		PTE0		UART1_TX	RTC_CLKOUT	CMP0_OUT	I2C1_SDA	
2	2	-	2	PTE1	DISABLED		PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	
3	_	-	_	PTE2	DISABLED		PTE2	SPI1_SCK					
4	_	-	_	PTE3	DISABLED		PTE3	SPI1_MISO			SPI1_MOSI		
5	-	-	_	PTE4	DISABLED		PTE4	SPI1_PCS0					
6	-	-	_	PTE5	DISABLED		PTE5						
7	3	1	-	VDD	VDD	VDD							
8	4	2	-	VSS	VSS	VSS							
9	5	3	3	PTE16	ADC0_DP1/ ADC0_SE1	ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_CLKIN0			
10	6	4	4	PTE17	ADC0_DM1/ ADC0_SE5a	ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_CLKIN1		LPTMR0_ ALT3	
11	7	5	5	PTE18	ADC0_DP2/ ADC0_SE2	ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		
12	8	6	6	PTE19	ADC0_DM2/ ADC0_SE6a	ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI		
13	9	7	_	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
14	10	8	-	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
15	11	-	-	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
16	12	_	-	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
17	13	9	7	VDDA	VDDA	VDDA							
18	14	10	-	VREFH	VREFH	VREFH							
19	15	11	-	VREFL	VREFL	VREFL							
20	16	12	8	VSSA	VSSA	VSSA							
21	17	13	-	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_CLKIN0			
22	18	14	9	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_CLKIN1			
23	19	-	_	PTE31	DISABLED		PTE31		TPM0_CH4				
24	20	15	-	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
25	21	16	_	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
26	22	17	10	PTA0	SWD_CLK	TSI0_CH1	PTA0		TPM0_CH5				SWD_CLK
27	23	18	11	PTA1	DISABLED	TSI0_CH2	PTA1	UART0_RX	TPM2_CH0				
28	24	19	12	PTA2	DISABLED	TSI0_CH3	PTA2	UART0_TX	TPM2_CH1				

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
29	25	20	13	PTA3	SWD_DIO	TSI0_CH4	PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
30	26	21	14	PTA4	NMI_b	TSI0_CH5	PTA4	I2C1_SDA	TPM0_CH1				NMI_b
31	27	-	-	PTA5	DISABLED		PTA5		TPM0_CH2				
32	28	_	-	PTA12	DISABLED		PTA12		TPM1_CH0				
33	29	_	_	PTA13	DISABLED		PTA13		TPM1_CH1				
34	_	_	_	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX				
35	_	_	_	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX				
36	_	_	_	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO		
37	_	-	-	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI		
38	30	22	15	VDD	VDD	VDD							
39	31	23	16	VSS	VSS	VSS							
40	32	24	17	PTA18	EXTALO	EXTALO	PTA18		UART1_RX	TPM_CLKIN0			
41	33	25	18	PTA19	XTALO	XTALO	PTA19		UART1_TX	TPM_CLKIN1		LPTMR0_ ALT1	
42	34	26	19	RESET_b	RESET_b		PTA20						
43	35	27	20	PTB0/ LLWU_P5	ADC0_SE8/ TSI0_CH0	ADC0_SE8/ TSI0_CH0	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
44	36	28	21	PTB1	ADC0_SE9/ TSI0_CH6	ADC0_SE9/ TSI0_CH6	PTB1	I2C0_SDA	TPM1_CH1				
45	37	29	-	PTB2	ADC0_SE12/ TSI0_CH7	ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	TPM2_CH0				
46	38	30	_	PTB3	ADC0_SE13/ TSI0_CH8	ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	TPM2_CH1				
47	—	-	Ι	PTB8	DISABLED		PTB8		EXTRG_IN				
48	—	—	—	PTB9	DISABLED		PTB9						
49	-	-	Ι	PTB10	DISABLED		PTB10	SPI1_PCS0					
50	—	—	—	PTB11	DISABLED		PTB11	SPI1_SCK					
51	39	31	Ι	PTB16	TSI0_CH9	TSI0_CH9	PTB16	SPI1_MOSI	UART0_RX	TPM_CLKIN0	SPI1_MISO		
52	40	32	—	PTB17	TSI0_CH10	TSI0_CH10	PTB17	SPI1_MISO	UART0_TX	TPM_CLKIN1	SPI1_MOSI		
53	41	-	-	PTB18	TSI0_CH11	TSI0_CH11	PTB18		TPM2_CH0				
54	42	—	—	PTB19	TSI0_CH12	TSI0_CH12	PTB19		TPM2_CH1				
55	43	33	-	PTC0	ADC0_SE14/ TSI0_CH13	ADC0_SE14/ TSI0_CH13	PTC0		EXTRG_IN		CMP0_OUT		
56	44	34	22	PTC1/ LLWU_P6/ RTC_CLKIN	ADC0_SE15/ TSI0_CH14	ADC0_SE15/ TSI0_CH14	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0			
57	45	35	23	PTC2	ADC0_SE11/ TSI0_CH15	ADC0_SE11/ TSI0_CH15	PTC2	I2C1_SDA		TPM0_CH1			
58	46	36	24	PTC3/ LLWU_P7	DISABLED		PTC3/ LLWU_P7		UART1_RX	TPM0_CH2	CLKOUT		
59	47	-	-	VSS	VSS	VSS							
60	48	-	-	VDD	VDD	VDD							
61	49	37	25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	TPM0_CH3			



Figure 17. KL15 80-pin LQFP pinout diagram